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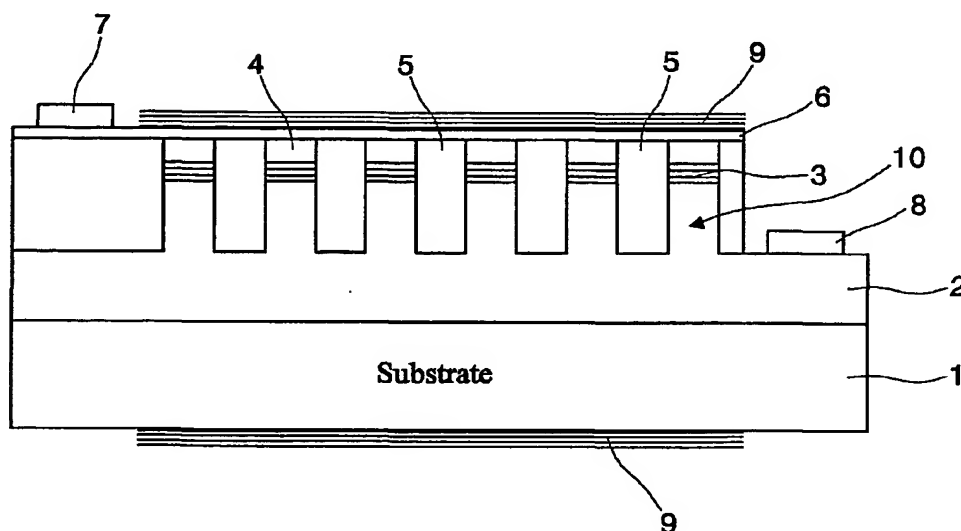
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- (71) Applicant (for all designated States except US): **VICHEL INC.** [KR/KR]; 3Fl. Jang Bldg. 92-6, Yangjae1-dong, Seocho-gu, Seoul 137-890 (KR).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): **KANG, Sang-kyu** [KR/KR]; 208-302 Moklyun apt., 1052, Hogae-dong, Dongan-ku, Anyang-City, Gyeonggi-do 431-080 (KR).
- (74) Agents: **KIM, Dong-Jin et al.**; Marcopolo Bldg 3F, 720-20 Yeoksam-Dong, Gangnam-gu, Seoul 135-080 (KR).
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(54) Title: **NITRIDE MICRO LIGHT EMITTING DIODE WITH HIGH BRIGHTNESS AND METHOD OF MANUFACTURING THE SAME**



(57) Abstract: The present invention relates to a nitride micro light emitting diode (LED) with high brightness and a method of manufacturing the same. The present invention provides a nitride micro LED with high brightness and a method of manufacturing the same, wherein a plurality of micro-sized luminous pillars 10 are formed in a substrates, a gap filling material such as SiO₂, Si₃N₄, DBR(ZrO₂/SiO₂ HfO₂/SiO₂), polyamide or the like is filled in gaps between the micro-sized luminous pillars, a top surface 11 of the luminous pillar array and the gap filling material is planarized through a CMP processing, and then a transparent electrode 6 having a large area is formed thereon, so that all the luminous pillars can be driven at the same time. In addition, the present invention provides a nitride micro LED with high brightness in which uniformity in formation of electrodes on the micro-sized luminous pillars array is enhanced by employing a flip-chip structure.